

SQD40P10-40L-GE3-VB Datasheet

P-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	- 100
$R_{DS(on)}$ (Ω) at $V_{GS} = - 10$ V	0.033
$R_{DS(on)}$ (Ω) at $V_{GS} = - 4.5$ V	0.036
I_D (A)	- 40
Configuration	Single

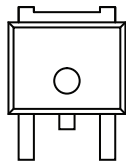
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE

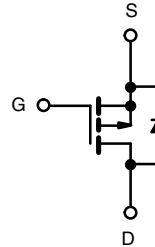
TO-252



G D S

Top View

Drain Connected to Tab



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	- 100	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	$T_C = 25$ °C	I_D	- 40	A
	$T_C = 125$ °C		- 22	
Continuous Source Current (Diode Conduction) ^a		I_S	- 50	
Pulsed Drain Current ^b		I_{DM}	- 150	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	- 44	
Single Pulse Avalanche Energy		E_{AS}	96	mJ
Maximum Power Dissipation ^b	$T_C = 25$ °C	P_D	136	W
	$T_C = 125$ °C		45	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	50	°C/W
Junction-to-Case (Drain)		R_{thJC}	1.1	

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR-4 material).
- Parametric verification ongoing.

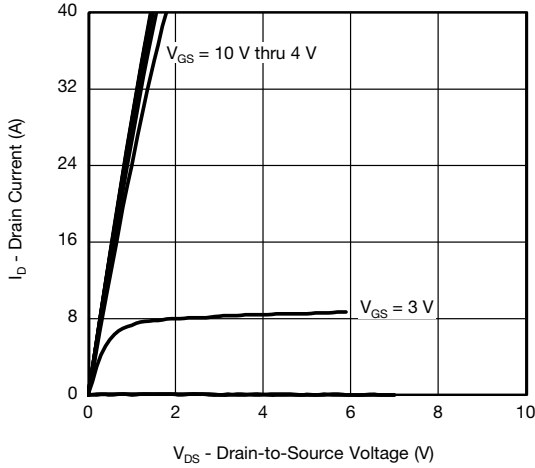
SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA		- 100	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA		- 1.0	-	-2.5	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = - 100 V	-	-	- 1	μA
		V _{GS} = 0 V	V _{DS} = - 100 V, T _J = 125 °C	-	-	- 50	
		V _{GS} = 0 V	V _{DS} = - 100 V, T _J = 175 °C	-	-	- 250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 10 V	V _{DS} ≤ - 5 V	- 30	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 9.2 A	-	0.033	-	Ω
		V _{GS} = - 10 V	I _D = - 9.2 A, T _J = 125 °C	-	0.065	-	
		V _{GS} = - 10 V	I _D = - 9.2 A, T _J = 175 °C	-	0.081	-	
		V _{GS} = - 4.5 V	I _D = - 7.7 A	-	0.037	-	
Forward Transconductance ^b	g _{fs}	V _{DS} = - 15 V, I _D = - 9.2 A		-	35	-	S
Dynamic^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = - 25 V, f = 1 MHz	-	4433	-	pF
Output Capacitance	C _{oss}			-	301	-	
Reverse Transfer Capacitance	C _{rss}			-	208	-	
Total Gate Charge ^c	Q _g	V _{GS} = - 10 V	V _{DS} = - 50V, I _D = - 9.2 A	-	96	144	nC
Gate-Source Charge ^c	Q _{gs}			-	8.4	-	
Gate-Drain Charge ^c	Q _{gd}			-	23.5	-	
Gate Resistance	R _g	f = 1 MHz		1.5	3.13	4.7	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = - 50 V, R _L = 6.49 Ω I _D ≅ - 7.7 A, V _{GEN} = - 10 V, R _g = 1.0 Ω		-	11	17	ns
Rise Time ^c	t _r			-	11	17	
Turn-Off Delay Time ^c	t _{d(off)}			-	78	117	
Fall Time ^c	t _f			-	15	23	
Source-Drain Diode Ratings and Characteristics^b							
Pulsed Current ^a	I _{SM}			-	-	- 150	A
Forward Voltage	V _{SD}	I _F = - 7.7 A, V _{GS} = 0 V		-	- 0.8	- 1.5	V

Notes

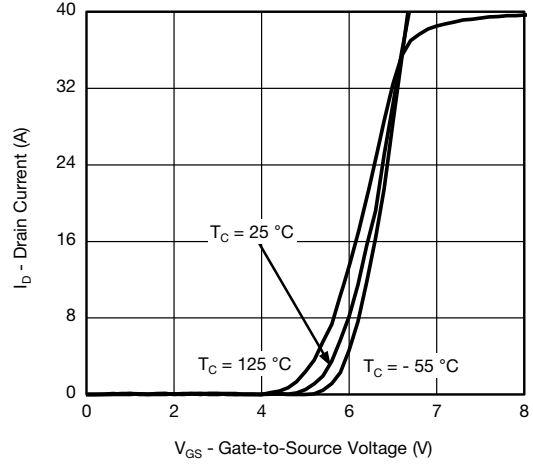
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

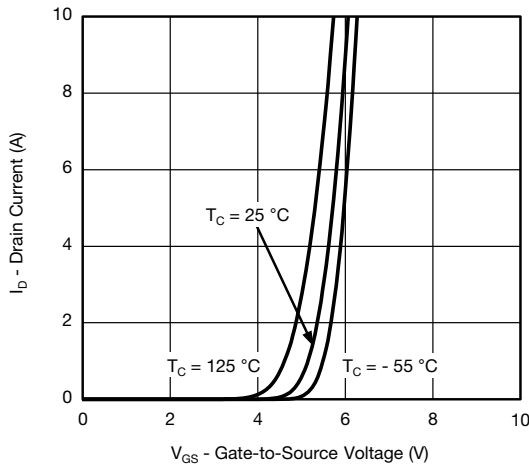
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



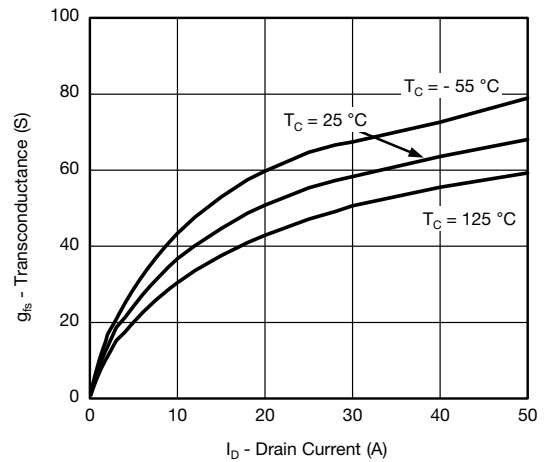
Output Characteristics



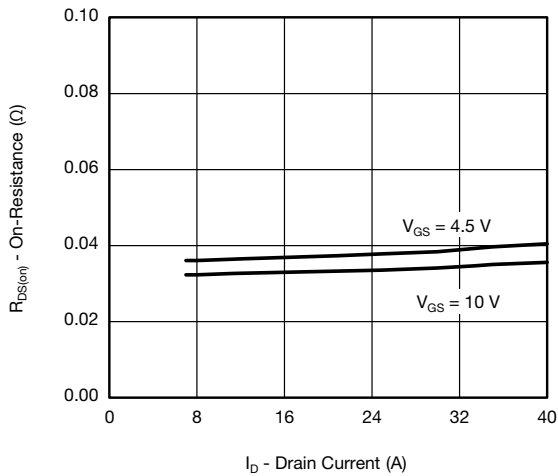
Transfer Characteristics



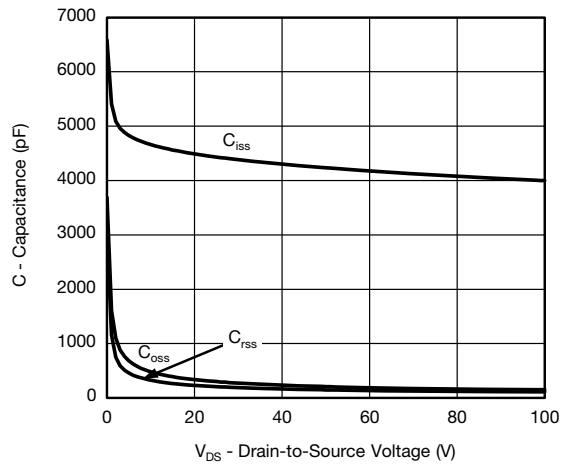
Transfer Characteristics



Transconductance

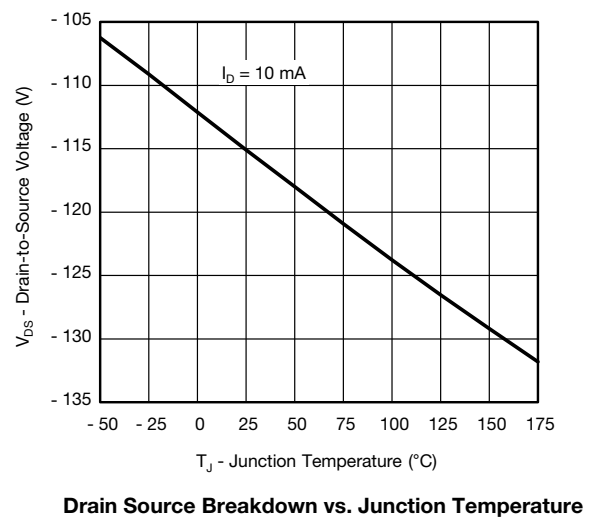
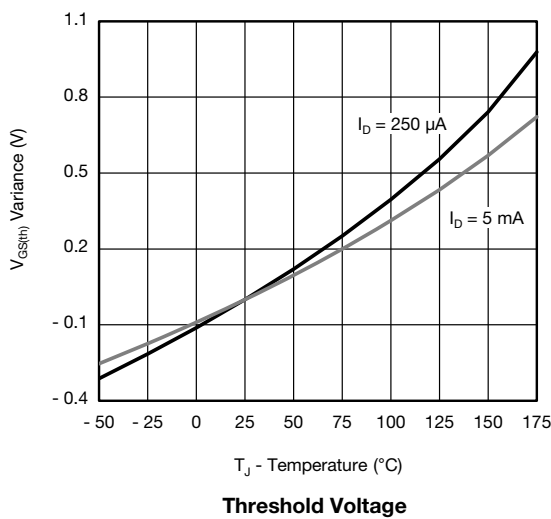
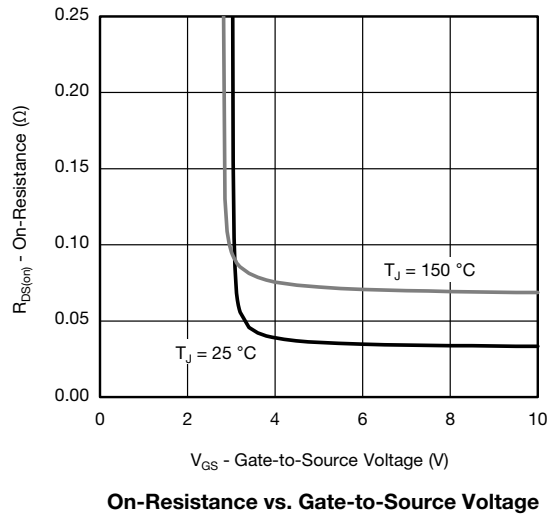
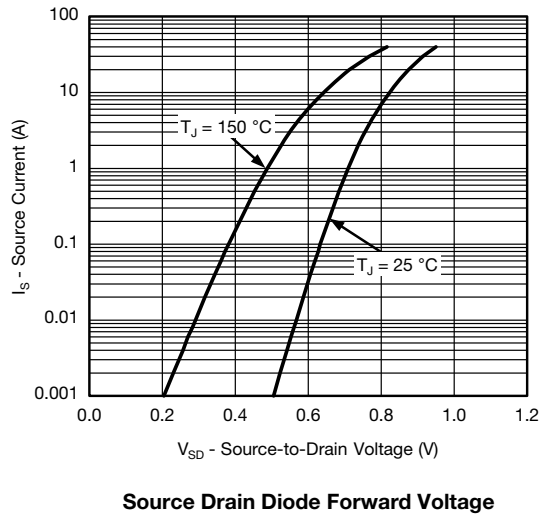
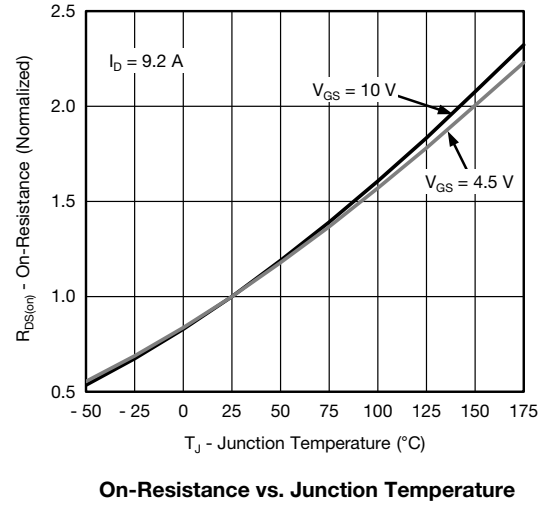
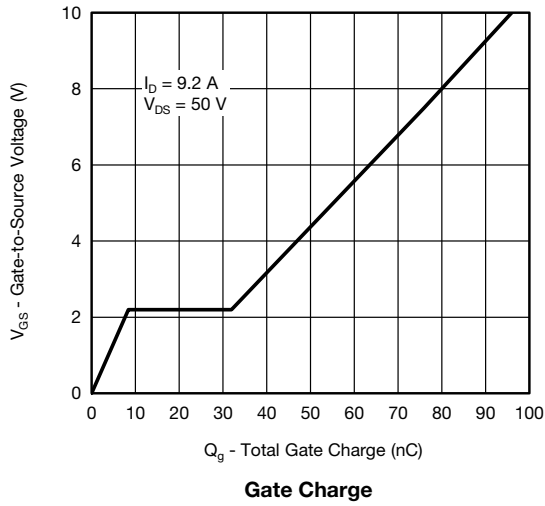


On-Resistance vs. Drain Current

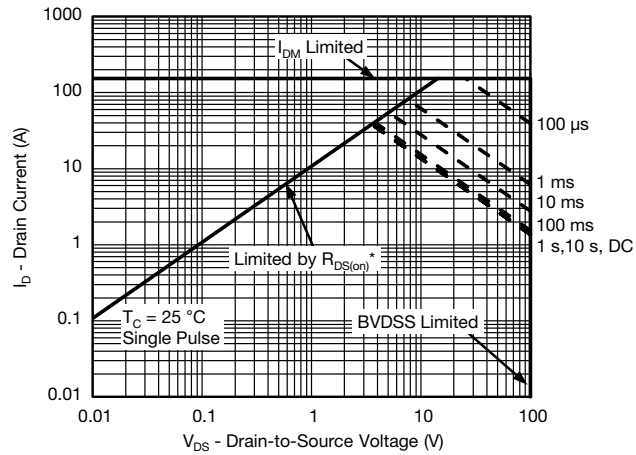


Capacitance

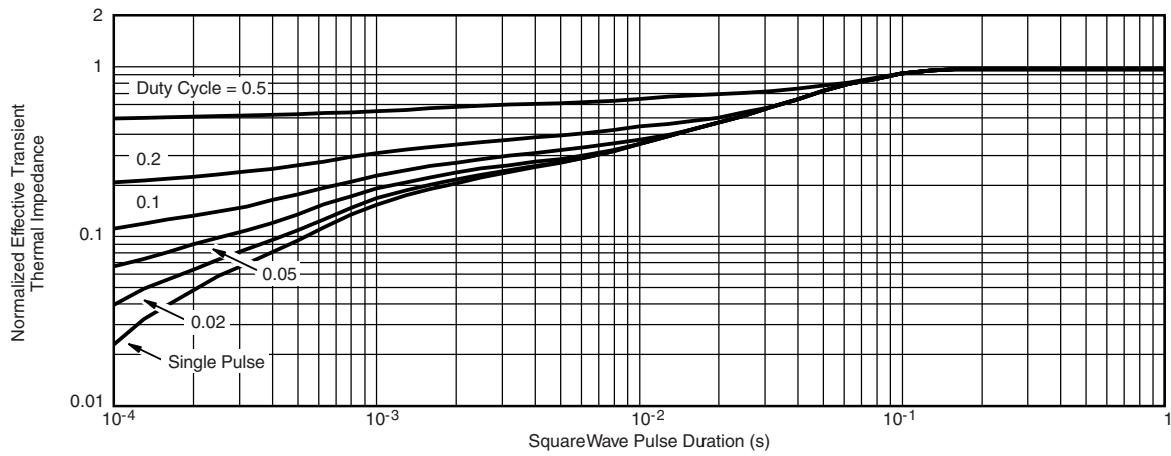
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

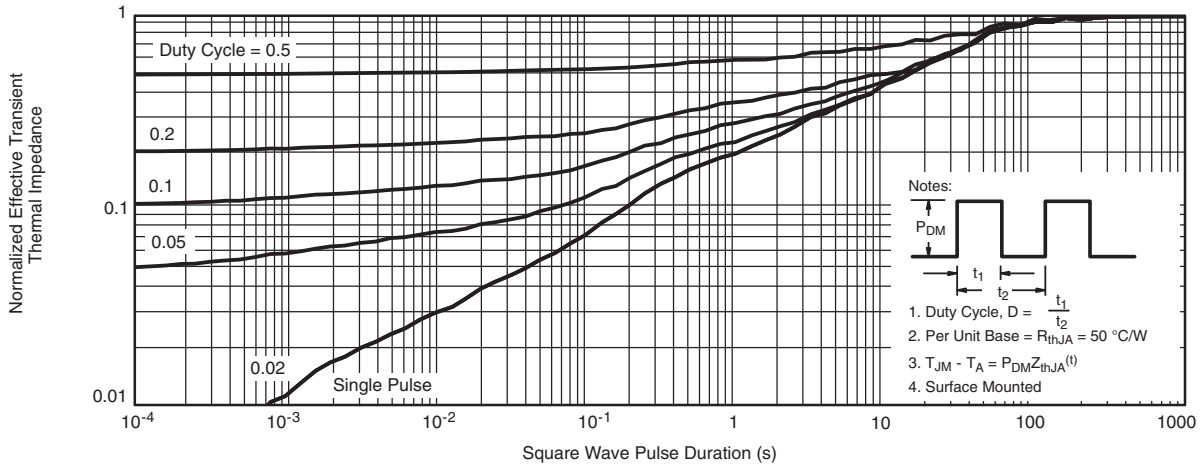


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

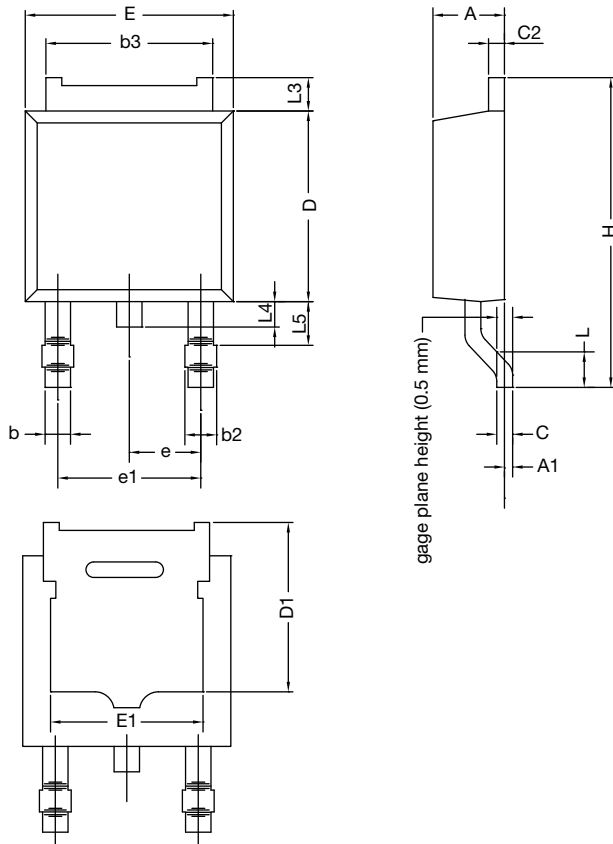


Normalized Thermal Transient Impedance, Junction-to-Ambient

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient ($25\text{ }^\circ\text{C}$)
 - Normalized Transient Thermal Impedance Junction to Case ($25\text{ }^\circ\text{C}$)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

TO-252AA Case Outline

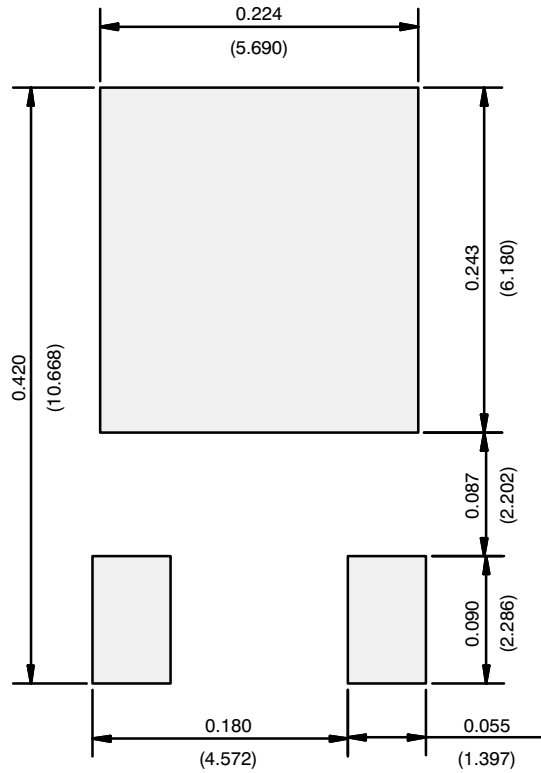


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	4.10	-	0.161	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.01	1.52	0.040	0.060
ECN: T13-0592-Rev. A, 02-Sep-13 DWG: 6019				

Note

- Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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